

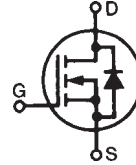
# HiPerFET™ Power MOSFETs Q-Class

**IXFH 30N60Q**  
**IXFT 30N60Q**

**V<sub>DSS</sub> = 600 V**  
**I<sub>D25</sub> = 30 A**  
**R<sub>DS(on)</sub> = 0.23 Ω**

N-Channel Enhancement Mode  
Avalanche Rated, High dv/dt, Low Q<sub>g</sub>

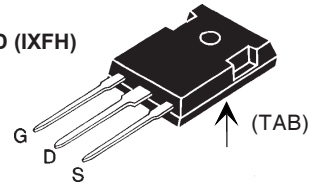
Preliminary Data Sheet



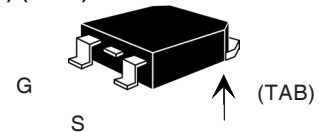
**t<sub>rr</sub> ≤ 250 ns**

Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	600	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C; R <sub>GS</sub> = 1 MΩ	600	V
V <sub>GS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	30	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	120	A
I <sub>AR</sub>	T <sub>C</sub> = 25°C	30	A
E <sub>AR</sub>	T <sub>C</sub> = 25°C	45	mJ
E <sub>AS</sub>	T <sub>C</sub> = 25°C	1.5	J
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , di/dt ≤ 100 A/μs, V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C, R <sub>G</sub> = 2 Ω	10	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	500	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6 mm (0.063 in) from case for 10 s	300	°C
M <sub>d</sub>	Mounting torque	TO-247	1.13/10 Nm/lb.in.
Weight		TO-247	6 g
		TO-268	4 g

TO-247 AD (IXFH)



TO-268 (D3) (IXFT)



G = Gate  
S = Source

D = Drain  
TAB = Drain

## Features

- Low gate charge
- International standard packages
- Epoxy meet UL 94 V-0, flammability classification
- Low R<sub>DS(on)</sub> HD MOS™ process
- Rugged polysilicon gate cell structure
- Avalanche energy and current rated
- Fast intrinsic Rectifier

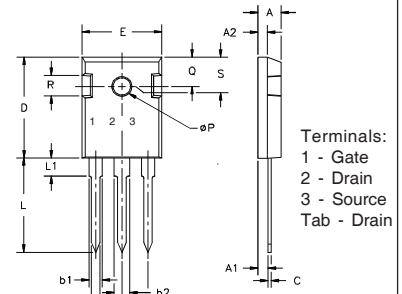
## Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values (T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
V <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA Temperature Coefficient	600	0.095	V %/K
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 4 mA Temperature Coefficient	2.5	- 0.24	V %/K
I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V <sub>DC</sub> , V <sub>DS</sub> = 0			±200 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> , T <sub>J</sub> = 25°C V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125°C			25 μA 1 mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			0.23 Ω

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ , pulse test	14	22	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4700	pF
$C_{oss}$			580	pF
$C_{rss}$			230	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2.0\ \Omega$ (External),		30	ns
$t_r$			32	ns
$t_{d(off)}$			80	ns
$t_f$			16	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		125	nC
$Q_{gs}$			28	nC
$Q_{gd}$			76	nC
$R_{thJC}$			0.25	K/W
$R_{thCK}$	TO-247		0.25	K/W

### TO-247 AD (IXFH) Outline



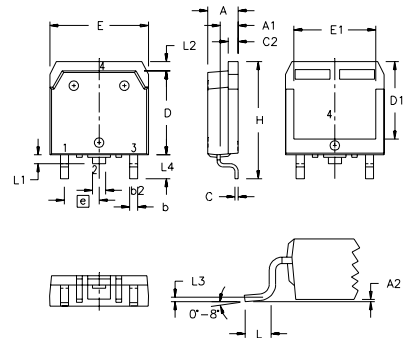
Terminals:  
1 - Gate  
2 - Drain  
3 - Source  
Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

### Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			26 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			104 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = I_S - di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		1	250 ns
$Q_{RM}$			10	$\mu\text{C}$
$I_{RM}$				A

### TO-268 Outline

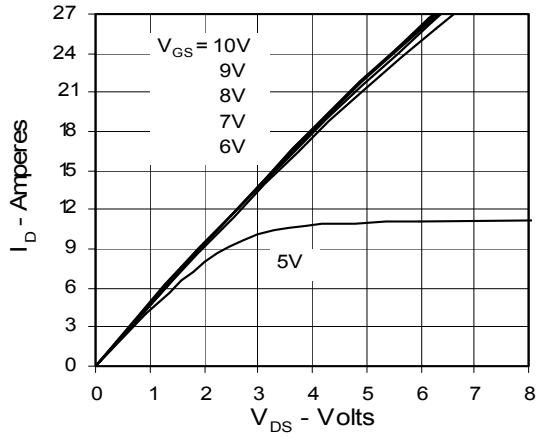


Terminals:  
1 - Gate  
2 - Drain  
3 - Source  
Tab - Drain

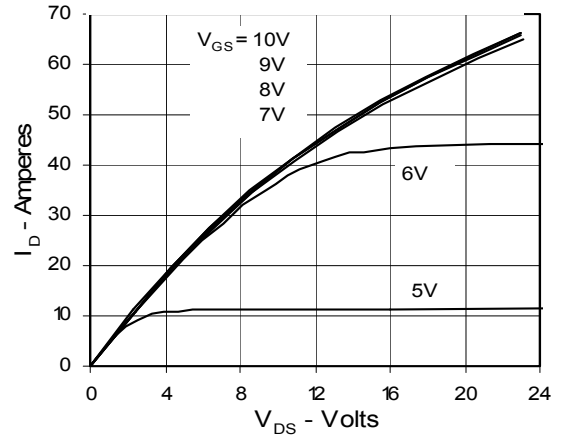
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A <sub>1</sub>	.106	.114	2.70	2.90
A <sub>2</sub>	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b <sub>2</sub>	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C <sub>2</sub>	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D <sub>1</sub>	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E <sub>1</sub>	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L <sub>1</sub>	.047	.055	1.20	1.40
L <sub>2</sub>	.039	.045	1.00	1.15
L <sub>3</sub>	.010	BSC	0.25	BSC
L <sub>4</sub>	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

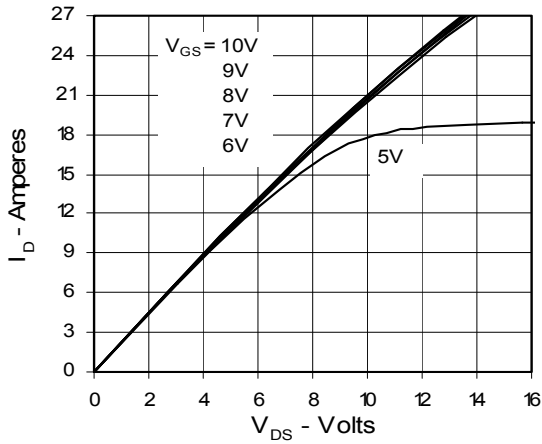
**Fig. 1. Output Characteristics**  
**@ 25 Deg. C**



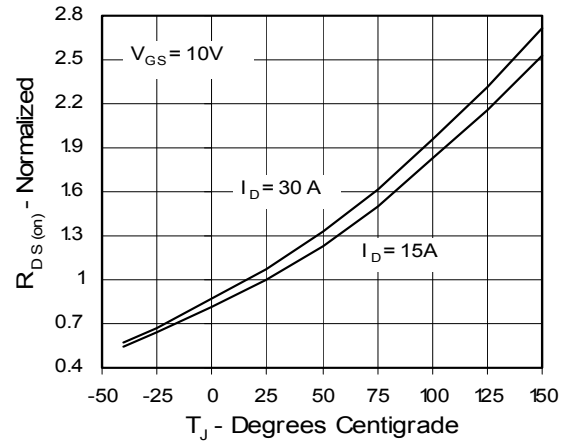
**Fig. 2. Extended Output Characteristics**  
**@ 25 deg. C**



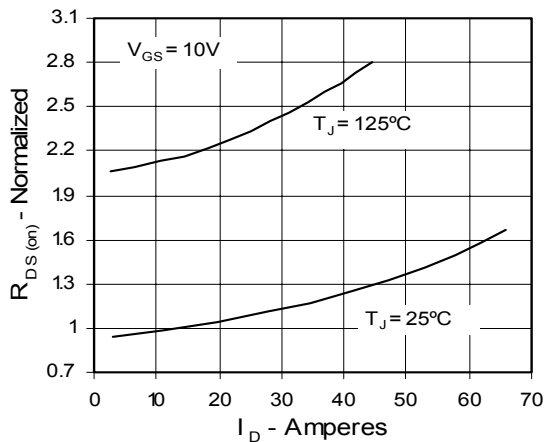
**Fig. 3. Output Characteristics**  
**@ 125 Deg. C**



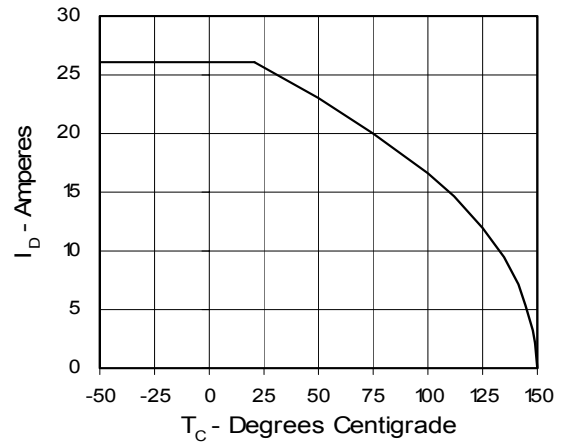
**Fig. 4. R\_DS(on) Normalized to I\_D25 Value vs. Junction Temperature**



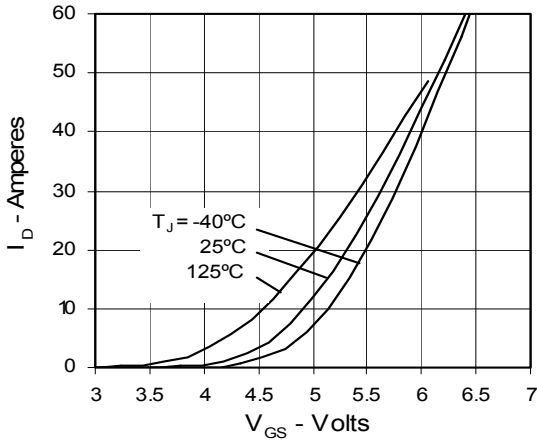
**Fig. 5. R\_DS(on) Normalized to I\_D25 Value vs. I\_D**



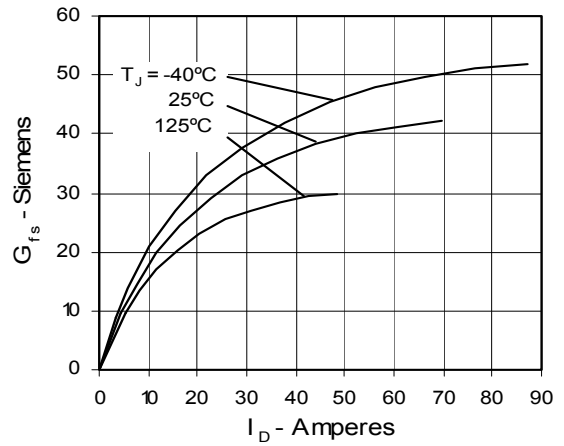
**Fig. 6. Drain Current vs. Case Temperature**



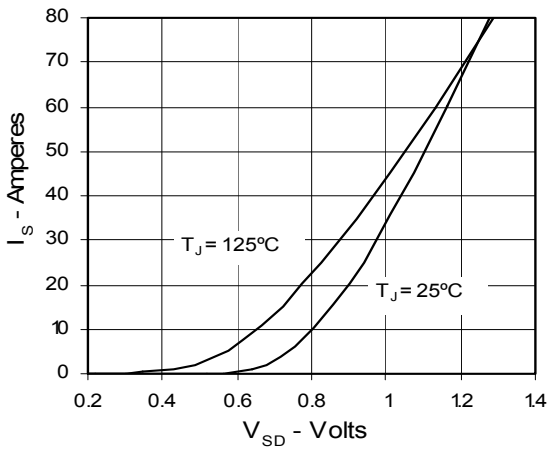
**Fig. 7. Input Admittance**



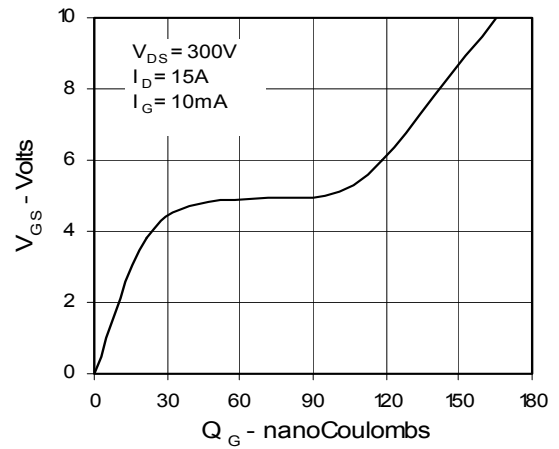
**Fig. 8. Transconductance**



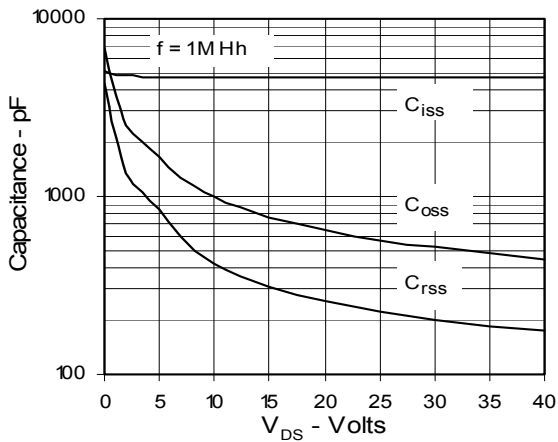
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



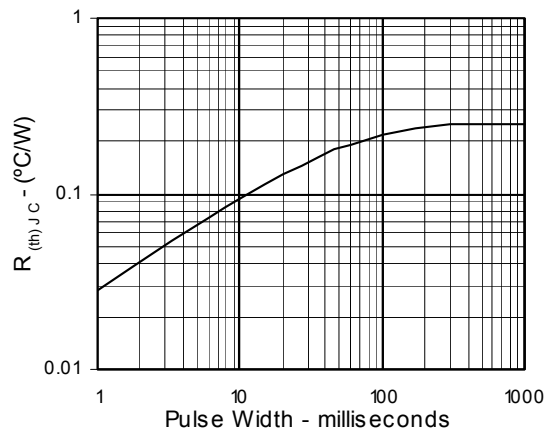
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Resistance**



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343